2. Amendments to the Specification

1. Please replace the paragraph that begins on page 7, line 3 with the following amended paragraph:

~~Fig. 1~~Fig. 1b shows a first embodiment of the method of preparing the nanotubes;

2. Please add the following paragraph immediately before the paragraph that begins on page 7, line 3:

Fig. 1a shows a known method of preparing nanostructures;

3. Please replace the paragraph that begins on page 8, line 3 with the following amended paragraph:

~~Fig. 1~~Fig. 1a shows schematically the temperature-dependent growth of the nanostructures. At relatively low substrate temperatures (<500 °C) the wire growth is limited by the crystal growth rate at the liquid-solid interface. The semiconductor species are homogeneously distributed throughout the liquid droplet and a solid semiconducting nanowire is formed. Fig. 1b shows schematically that ~~A~~at higher substrate temperatures (>500 °C) the reaction becomes diffusion-limited; the diffusion of semiconducting species through the liquid droplet is relatively slow compared to crystal growth. The concentration of the semiconductor species becomes depleted and for geometry reasons the crystal growth starts circularly. As a result, nanotubes having a crystalline mantle and a hollow core are formed. The applied substrate temperature determines the overall diameter of the tube and the mantle thickness.